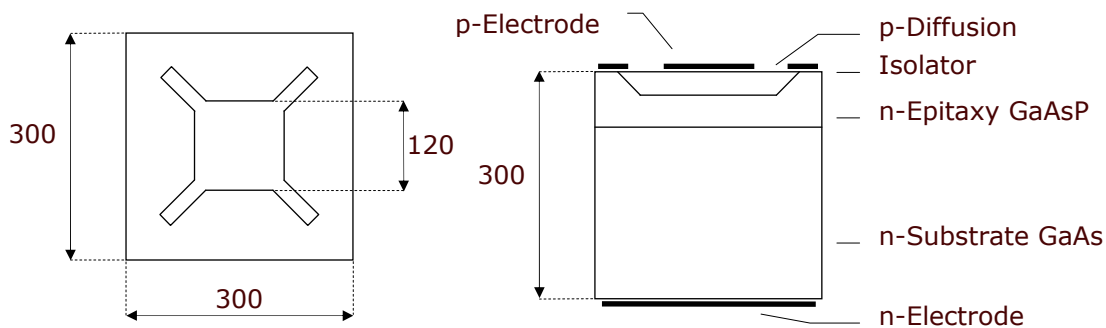


RED

Item No.: 101205

1. This specification applies to GaAsP / GaAs LED Chips
2. Structure
 - 2.1 Planar structure
 - 2.2 Electrodes

p-side (anode)	Al
n-side (cathode)	Au alloy
3. Outlines (dimensions in microns)



4. Electrical and optical characteristics (T=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage	V_F	$I_F = 20 \text{ mA}$		1,65	1,84	V
Reverse voltage	V_R	$I_R = 10 \text{ } \mu\text{A}$	5			V
Luminous intensity *	I_V	$I_F = 20 \text{ mA}$	300	600		μcd
Peak wavelength	λ_p	$I_F = 20 \text{ mA}$		660		nm

* On request, wafers will be delivered according to luminous intensity classes
Brightness measurement at OSA on gold plate

5. Packing

Dice on adhesive film with wire bond side on top
6. Labeling

Type	Lot No.	I_V typ min max	Quantity